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5 A F .

Symbol	Parameter	Max.	Units
$I_D @ T_c = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	172	
$I_D @ T_c = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	122	A




**F**

Symbol	Characteristics	Typ.	Max.	Units
	Junction-to-case			

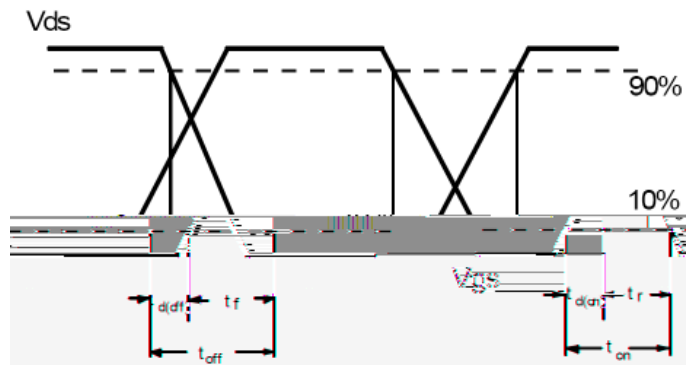
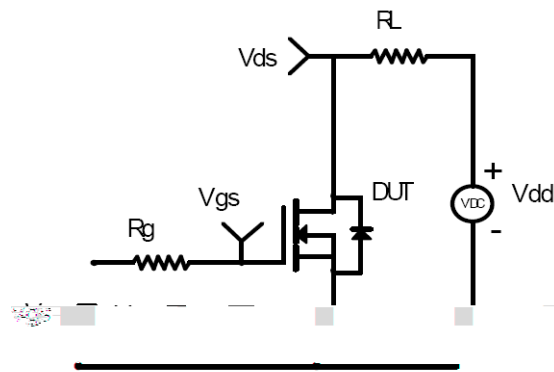
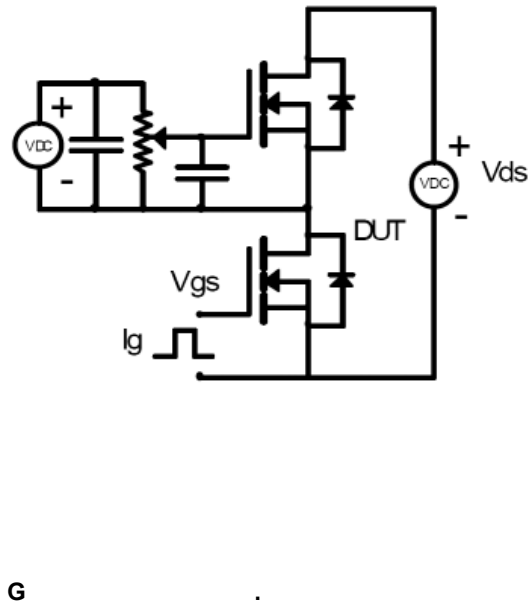
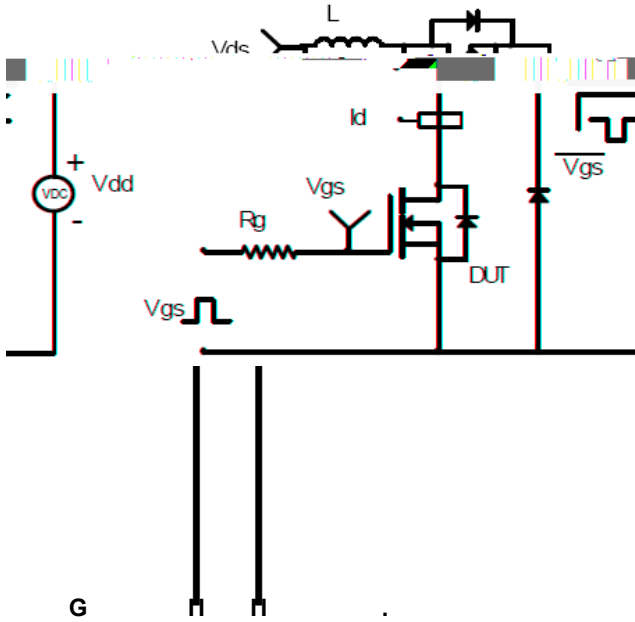
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	40			V	$V_{GS} = 0V, I_D$
$R_{DS(on)}$	Static Drain-to-Source on-resistance		2.1	2.4	m	$V_{GS}=10V, I_D=40A$
$V_{GS(th)}$	Gate threshold voltage	2		4	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$I_{DSS}$	Drain-to-Source leakage current $T_J=25^\circ C$			1		$V_{DS}=40V, V_{GS}=0V,$
$I_{GSS}$	Gate-to-Source forward leakage			100	nA	$V_{GS}=20V, V_{DS}=0V$
				-100		$V_{GS}=-20V, V_{DS}=0V$
$Q_g$	Total gate charge		140		nC	$T_J=25^\circ C, V_{GS}=10V,$ $V_{DS}=20V, I_D=20A$
$Q_{gs}$	Gate-to-Source charge		26			
$Q_{gd}$	Gate-to-Drain("Miller") charge		35			
$t_{d(on)}$	Turn-on delay time		30		ns	$V_{GS}=10V$ $V_{DS}=20V$ $R_G=3.6$ $R_{L_}$
$t_r$	Rise time		32			
$t_{d(off)}$	Turn-Off delay time		70			
$t_f$	Fall time		25			
$C_{iss}$	Input capacitance		10587		pF	$V_{GS}=0V$ $V_{DS}=40V$ $f=1MHz$
$C_{oss}$	Output capacitance		647			
$C_{rss}$	Reverse transfer capacitance		603			

**G -8 F**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)			172	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode)			688	A	
$V_{SD}$	Diode Forward Voltage			1.2	V	$I_S=40A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time		50		ns	$T_J = 25^\circ C, I_F = 20A, di/dt =$
$Q_{rr}$	Reverse Recovery Charge		75		nC	



5 GHz



**B**

Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation  $P_D$  is based on max. junction temperature, using junction-to-case thermal resistance.



Typical Electrical and Thermal Characteristics

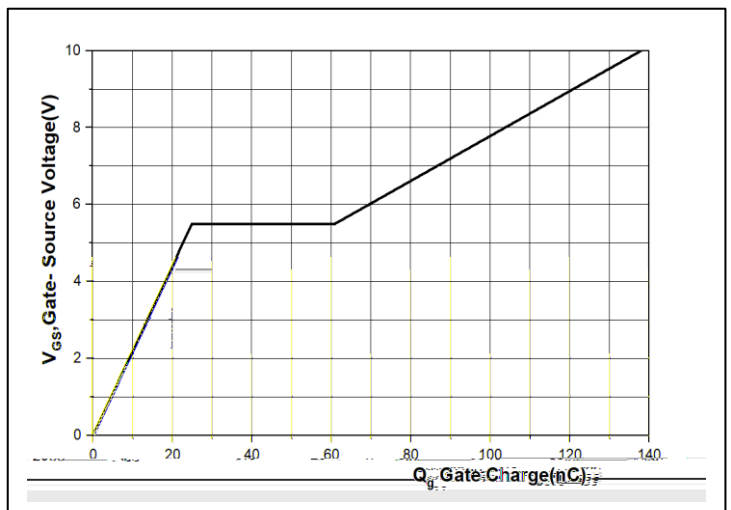
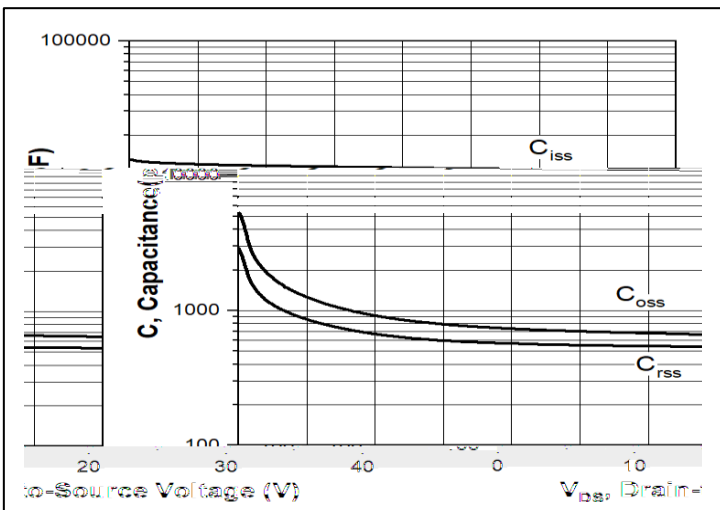
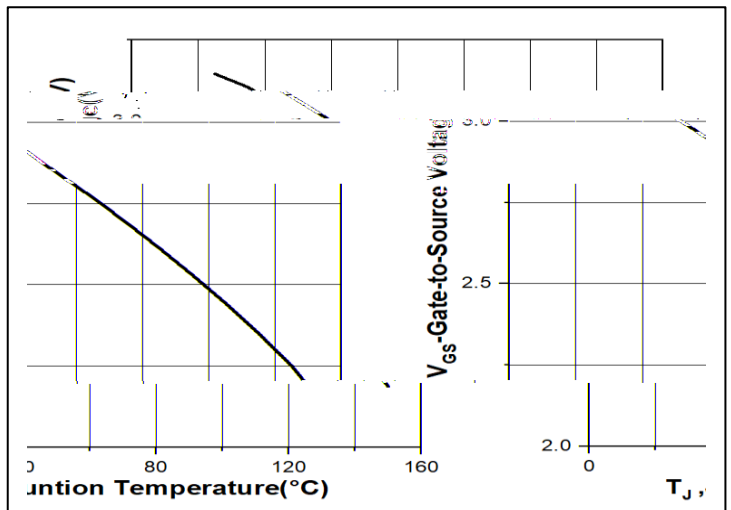
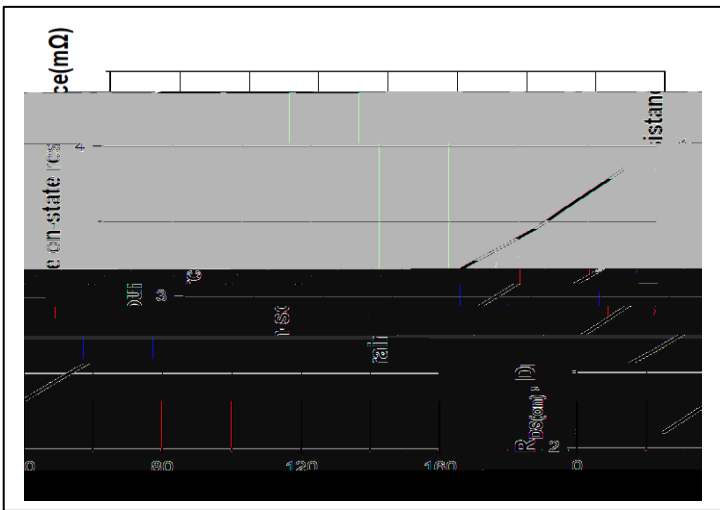
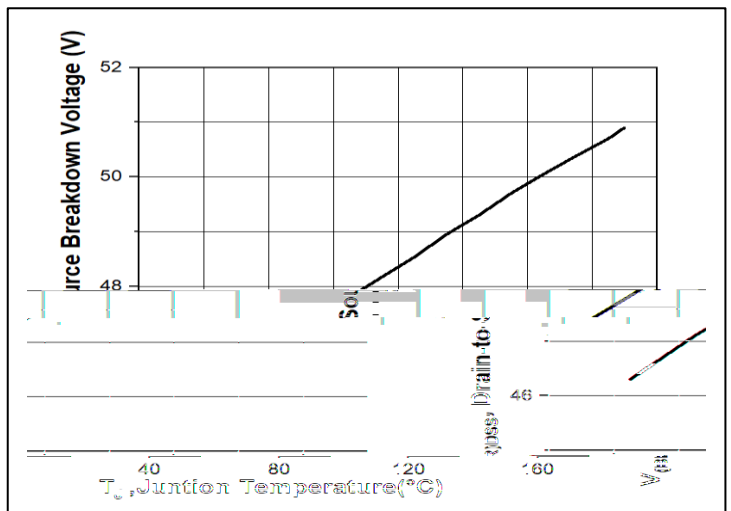
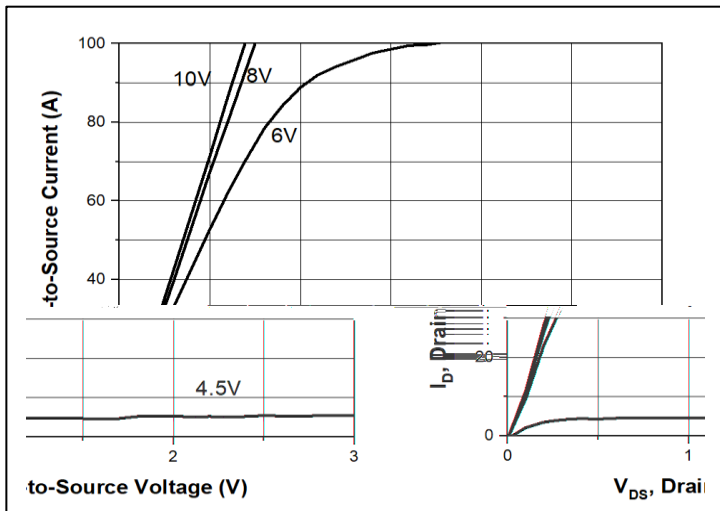
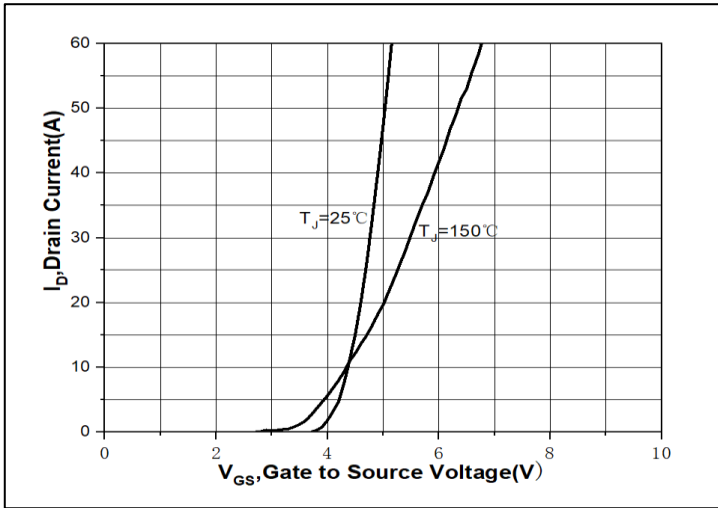


Figure5. Capacitance

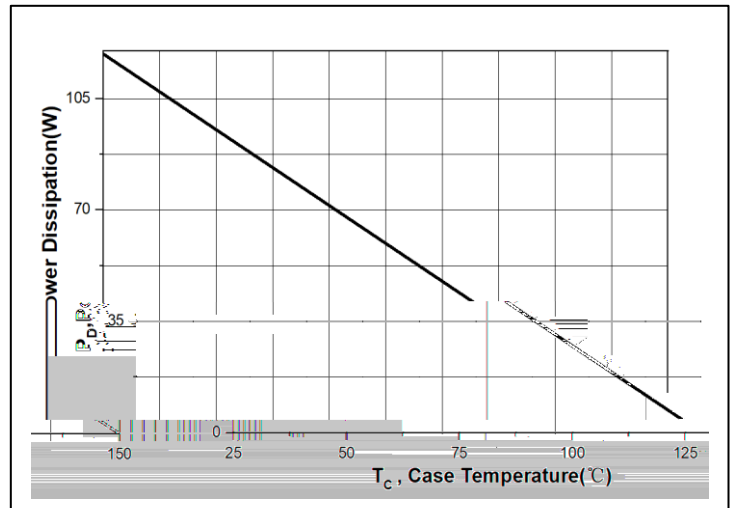
Figure6. Gate Charge



### Typical Electrical and Thermal Characteristics



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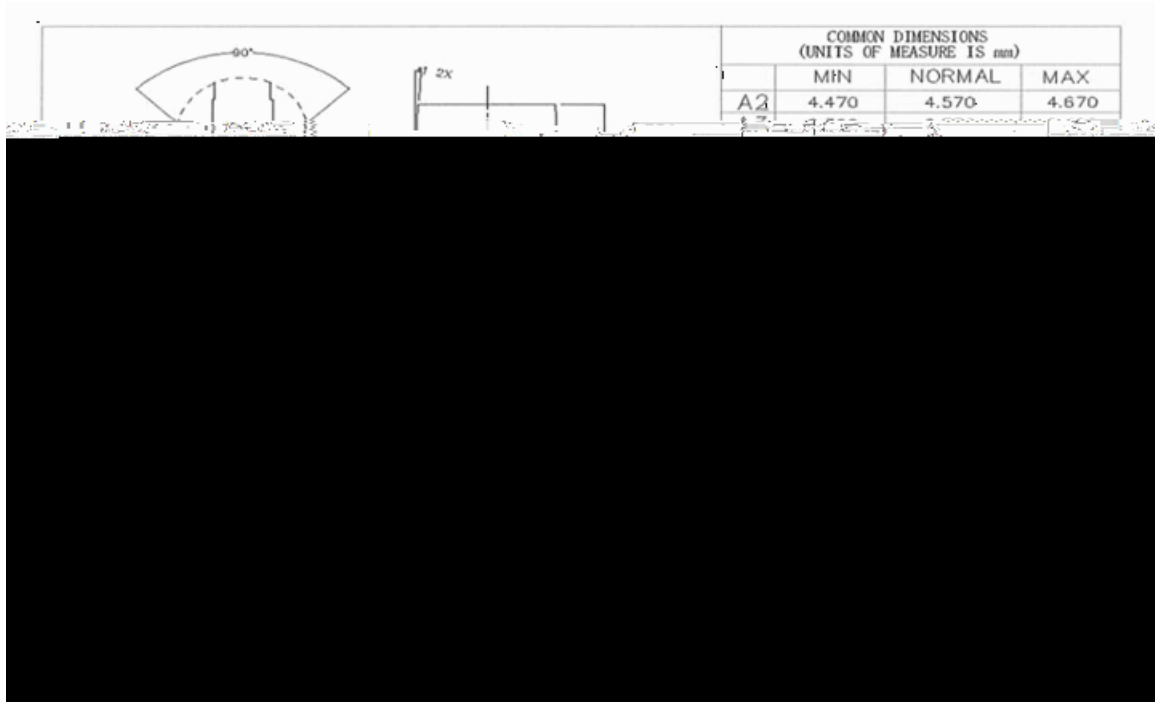


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A 8

Unit:mm





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